

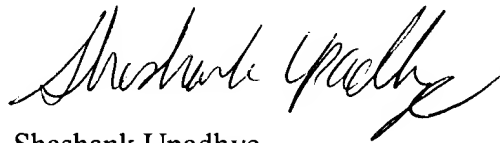
and nonobvious configuration is capable of high quality crystalline growth and reduced crystal dislocations (see pgs. 15, 16). Finally, the applicant also notes that the second mask 15 is removed as shown in FIG. 2A and 5A. Kiyoku '010 does not teach such removal of the mask.

With respect to the indefiniteness rejections, the applicant notes that claim 4 is sufficiently definite. In particular, it is noted that although the dissolving solution is unnamed, it is quite clear that the solution, whatever it is, is capable of dissolving the masks and not the under layers. The claim, when read in view of the specification on page 11, the solution capable of doing so is quite clear. The point of novelty of claim 4 is not simply due to the recitation of a dissolving step, rather, the novelty and subsequent nonobviousness rests in the recitations of claim 4 in conjunction with claim 3 and claim 1. To this end, the applicant is not required to list the litany of chemicals capable of specific material dissolutions.

Conclusion

The applicant respectfully requests withdrawal of the rejections and believes that the claims as presented represent allowable subject matter. But if the Examiner desires, the applicant is ready for a telephone interview to expedite prosecution. As always, the Examiner is free to call the undersigned at 312-876-2622.

Respectfully submitted,



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In the United States Patent and Trademark Office

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| | |) | |
| Serial No.: | 09/726,860 |) | |
| | |) | Group Unit: 1765 |
| | |) | |
| Title: | Method of Manufacturing Crystal of III-V... |) | |
| | |) | |
| Atty. Docket No. | 9792909-4715 |) | |

Response C to First Non Final Office Action dated 23 July 2002

In response to the Non Final Office Action dated 23 July 2002, the applicant responds as follows.

A. In the Claims

- 53E. > 1. (amended) A method of manufacturing a crystal of a III-V compound of the nitride system, the method including:
- a first growth step to form a first crystal layer, the first crystal layer further having a surface, by growing a crystal of a III-V compound of the nitride system on a surface of a basal
- D, body;
- a first mask forming step to form a first mask pattern on the surface of the first crystal layer;
- a first etching step to etch the first crystal layer through the first mask pattern;
- a second growth step to form a second crystal layer, the second crystal layer further having a surface, by growing a crystal of a III-V compound of the nitride system from the first crystal layer;
- a second mask forming step to form a second mask pattern on the surface of the second crystal layer and ensuring that the second mask overlies a window in the first mask;
- a second etching step to form the second crystal layer through the second mask pattern;

a third growth step to form a third crystal layer by growing a crystal of a III-V compound of the nitride system from the second crystal layer; and
between the second etching step and the third growth step, a step of removing at least part of the second mask pattern.

2. Canceled.

3. (Amended) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein the first mask pattern at least includes an under layer formed over the first crystal layer and an upper layer formed over the under layer.

4. (Amended) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 3,

wherein the upper layer of the first mask pattern, and the second mask pattern are formed of a material which can be dissolved by a solution, and

the under layer of the first mask pattern is formed of a material which cannot be dissolved by the solution.

5. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein windows of the first mask pattern and windows of the second mask pattern do not overlies one another in the direction of the thickness of the crystal.

6. (Canceled).

5/26/17
7. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1, further including:

D3
after the third growth step, a step of separating a portion of the crystal which includes at least the basal body, from the crystal.

8. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein an inner layer is formed at least in one of the first crystal layer, the second crystal layer and the third crystal layer, and the inner layer has a different composition from the crystal layer in which the inner layer is formed.

9. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 8,

wherein the inner layer includes a III-V compound of the nitride system.

10. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein each of the first mask pattern and the second mask pattern includes a plurality of pattern elements arranged in one direction in a plane almost parallel to the surface of the basal body.

11. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 10,

wherein both the pattern elements of the first mask pattern and the pattern elements of the second mask pattern are in the form of stripes.

12. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein each of the first mask pattern and the second mask pattern includes pattern elements arranged in two directions in a plane almost parallel to the surface of the basal body.

13. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein each of the first mask pattern and the second mask pattern includes silicon (Si) and at least one element selected from the group consisting of oxygen (O) and nitrogen (N).

14. A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 13,

wherein the basal body comprises at least one of a sapphire (Al_2O_3), silicon (Si), silicon carbide (SiC), gallium arsenide (GaAs), magnesium aluminum composite oxide (MgAl_2O_4), lithium gallium composite dioxide (LiGaO_2) and gallium nitride (GaN).

15. (Amended) A method of manufacturing a device, the method including a crystal growth step of forming a crystal substrate or a crystal film and comprising manufacturing a device by forming a device film over the crystal substrate or the crystal film,

wherein the crystal growth step includes:

a first growth step of forming a first crystal layer by growing a crystal of a III-V compound of the nitride system on the surface of a basal body;

a first mask forming step of forming a first mask pattern on the surface of the first crystal layer;

a first etching step of etching the first crystal layer through the first mask pattern;
a second growth step of forming a second crystal layer by growing a crystal of a III-V compound of the nitride system from the first crystal layer;
a second mask forming step of forming a second mask pattern on the surface of the second crystal layer and ensuring that the second mask overlies a window in the first mask;
a second etching step of etching the second crystal layer through the second mask pattern;
and
a third growth step of forming a third crystal layer by growing a crystal of a III-V compound of the nitride system from the second crystal layer.

16. A method of manufacturing a device as claimed in claim 15, further including a step of separating the basal body from the crystal substrate or the crystal film.